
2SC1345(K)

Silicon NPN Epitaxial

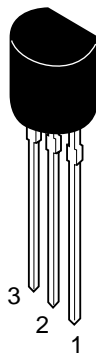
HITACHI

Application

Low frequency low noise amplifier

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SC1345 (K)

Absolute Maximum Ratings (Ta = 25°C)

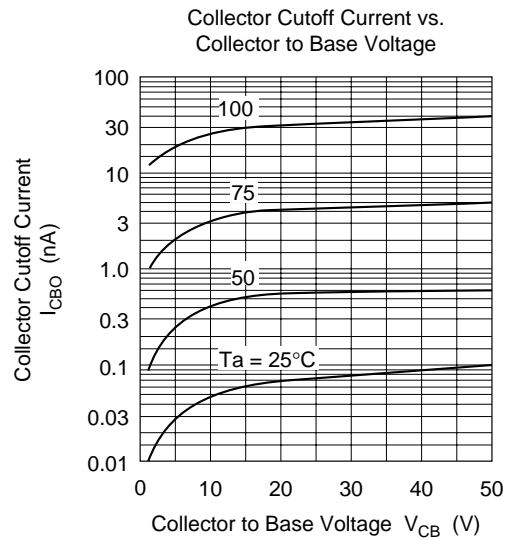
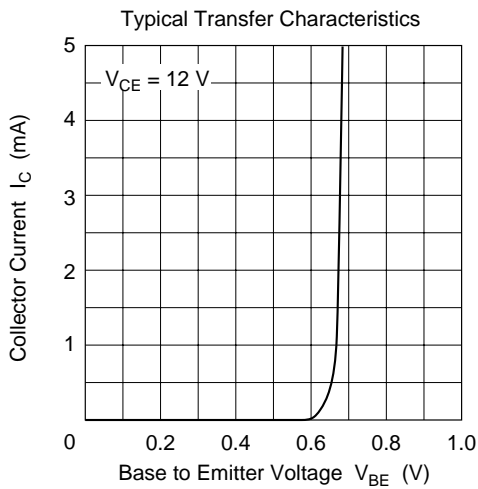
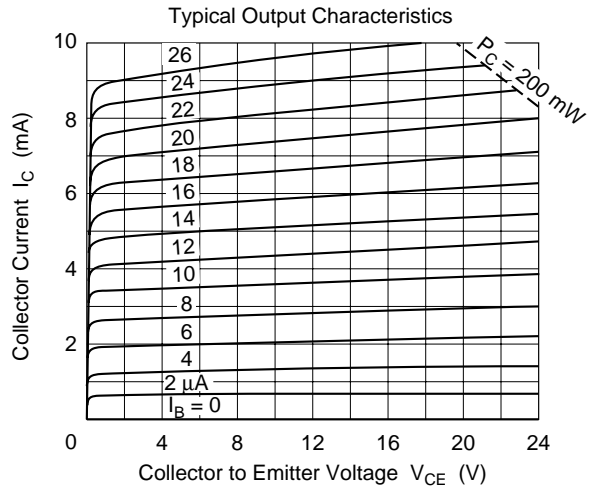
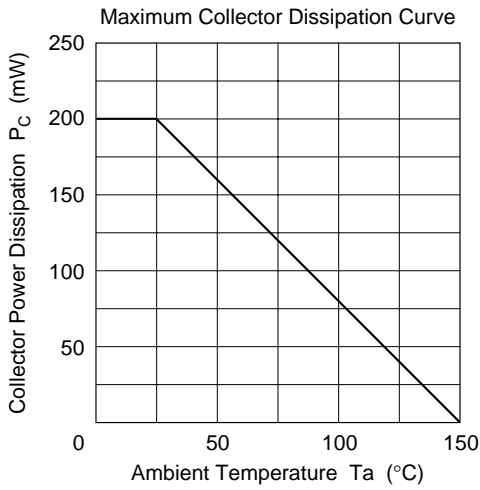
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	55	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

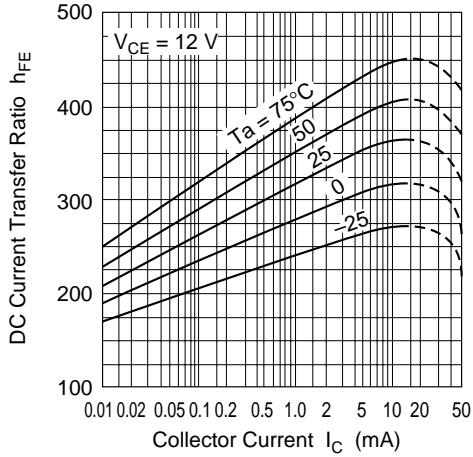
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	55	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 18 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	1200		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Collector output capacitance	C_{ob}	—	2.3	3.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
Gain bandwidth product	f_T	—	230	—	MHz	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Noise figure	NF	—	—	8	dB	$V_{CE} = 6 \text{ V}, I_C = 0.1 \text{ mA}, f = 10 \text{ Hz}, R_g = 10 \text{ k}\Omega$
		—	—	1	dB	$V_{CE} = 6 \text{ V}, I_C = 0.1 \text{ mA}, f = 1 \text{ kHz}, R_g = 10 \text{ k}\Omega$

Note: 1. The 2SC1345(K) is grouped by h_{FE} as follows.

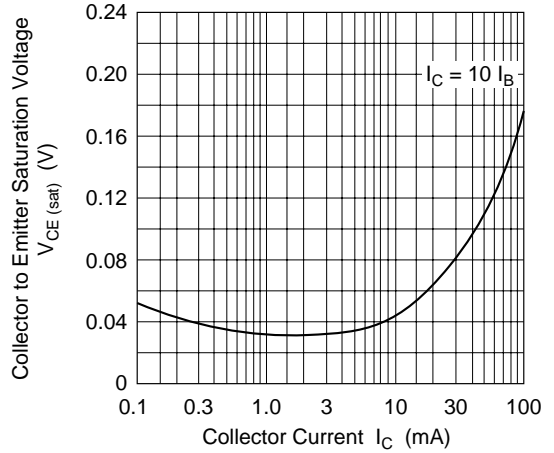
D	E	F
250 to 500	400 to 800	600 to 1200



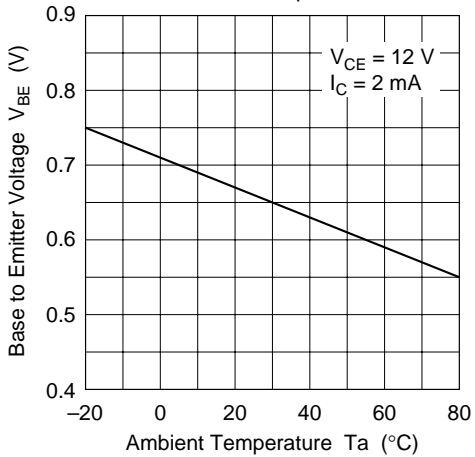
DC Current Transfer Ratio vs. Collector Current



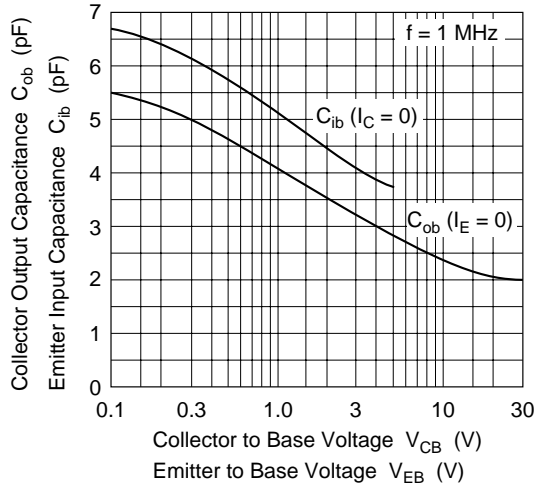
Collector to Emitter Saturation Voltage vs. Collector Current

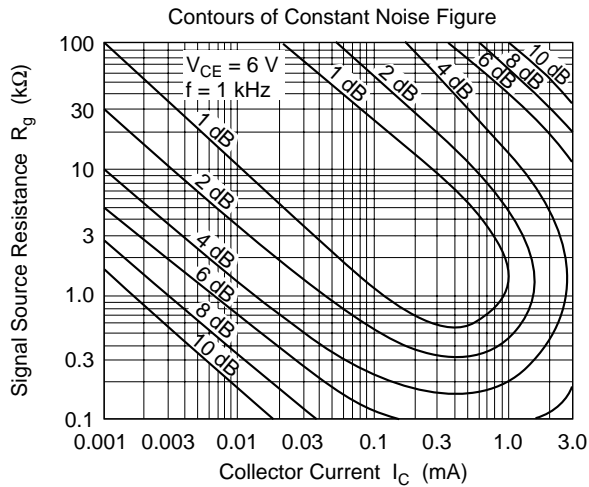
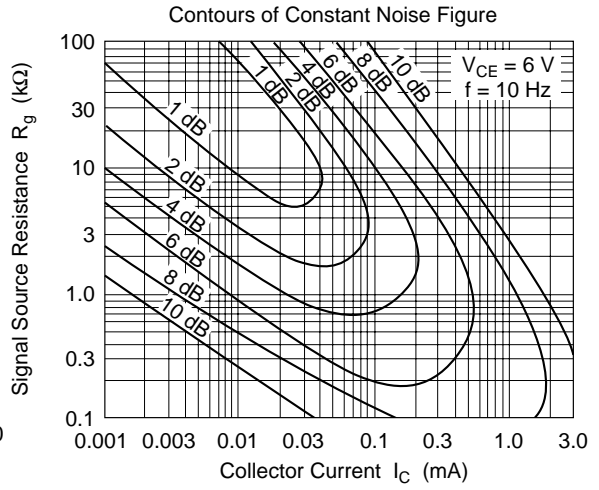
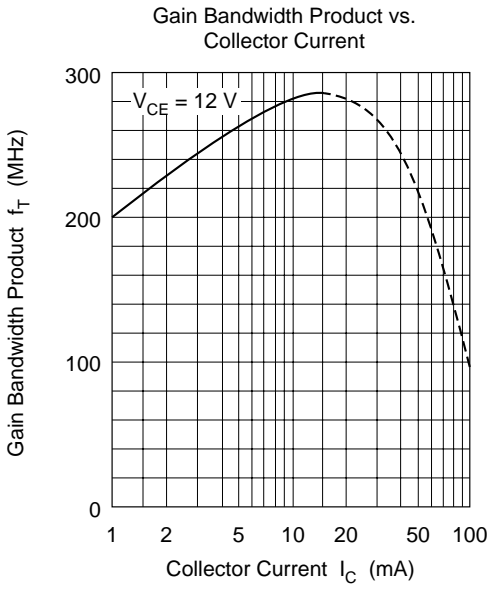


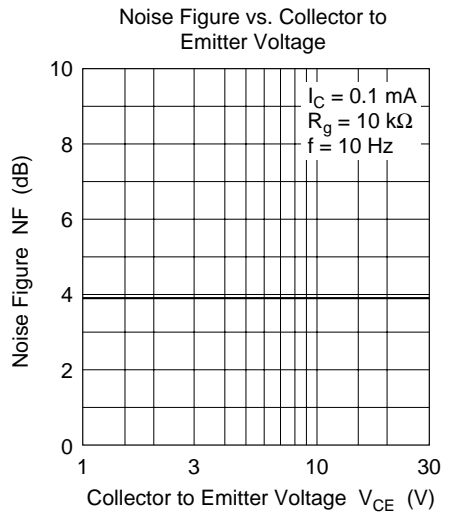
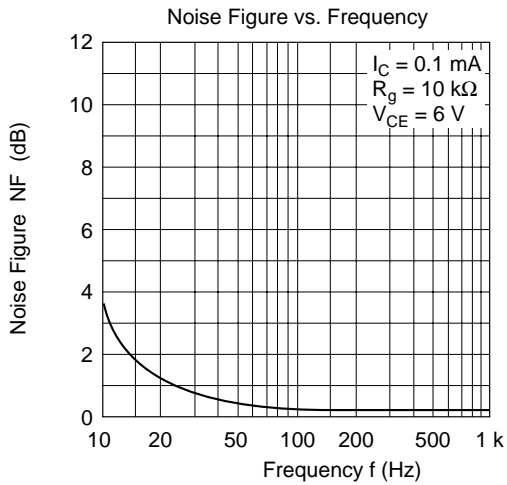
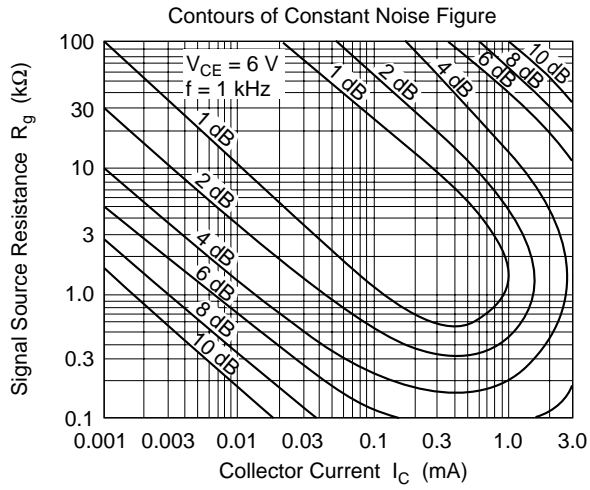
Base to Emitter Voltage vs. Ambient Temperature

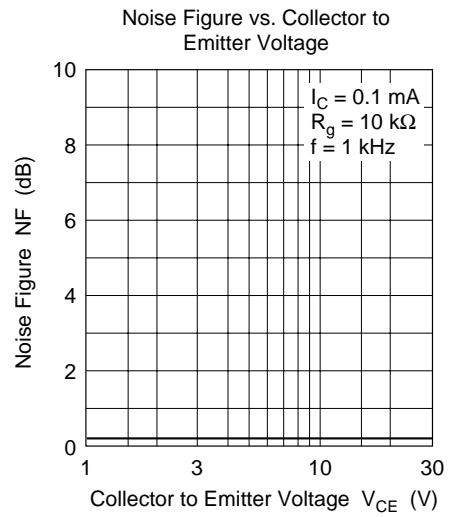
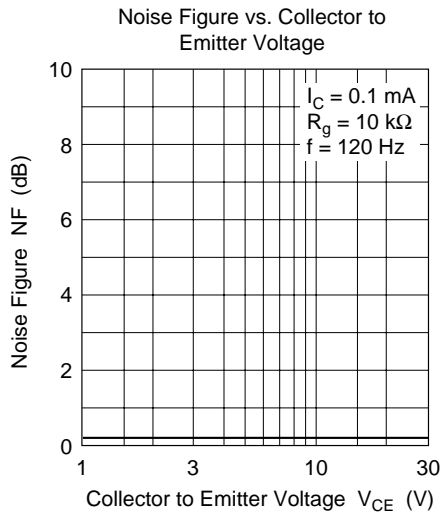


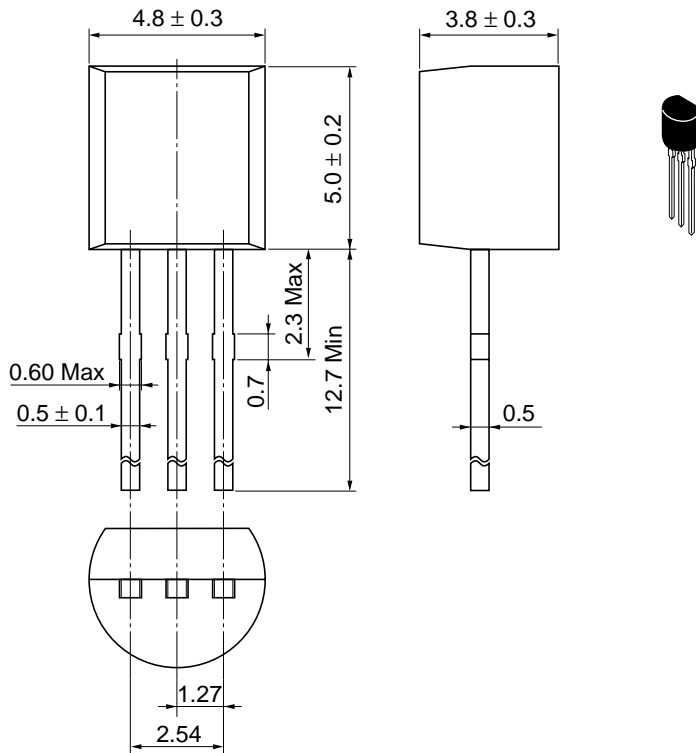
Input and Output Capacitance vs. Voltage











Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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